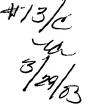
**DOCKET NO. 99-039** 





## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball,

Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

Appl. No.

09/464,297

Filed:

December 15, 1999

Title

PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF

OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND

AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U.

1765

Examiner

Charlotte A. Brown

Docket No.

99-039

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231

on March 20, 2003
(Date of Deposit)

John P. Taylor, Reg. No. 22,369

March 20, 2003

Date of Signature

## **AMENDMENT**

Honorable Commissioner for Patents Washington, D.C. 20231

Date: March 20, 2003

Sir:

In response to the Office Action mailed January 7, 2003, please amend the application as follows: